## DESCRIPTION

The $A 4770 \mathrm{~A}$ is an integrated $150 \mathrm{~m} \Omega$ power switch for self-powered and bus-powered Universal Series Bus (USB) applications. A built-in charge pump is used to drive the N -channel NMOSFET that is free of parasitic body diode to eliminate any reversed current flow across the switch when it is powered off. Its low quiescent supply current $(23 \mu \mathrm{~A})$ and small package (SOT-25) is particularly suitable in battery-powered portable equipment.

Several protection functions include soft start to limit inrush current during plug-in, current limiting at 1000 mA or 650 mA , and thermal shutdown to protect damage under over current conditions.

The A4770A is available in SOT-25 package.

ORDERING INFORMATION

| Package Type | Part Number |  |
| :---: | :---: | :--- |
| SOT-25 | E5 | A4770AE5R-X |
| SPQ:000pcs/Reel |  | A4770AE5VR-X |
| Note | X=Maximum Current |  |
|  |  |  |
|  | B=650mA |  |
|  | V: Halogen free Package |  |
|  | R: Tape \& Reel |  |
| AiT provides all RoHS products |  |  |

## FEATURES

- $150 \mathrm{~m} \Omega$ (Typ.) High-Side NMOSFET (SOT- 25)
- $650 \mathrm{~mA} / 1000 \mathrm{~mA}$ Current Limit (Typ)
- Small SOT- 25 Package Minimizes Board Space
- Soft Start
- Thermal Protection
- Low $23 \mu \mathrm{~A}$ Supply Current
- Wide Input Voltage Range: 2.2V ~6V
- Available in SOT-25 package


## APPLICATION

- Battery-Powered Equipment
- Motherboard USB Power Switch
- USB Device Power Switch
- Hot-Plug Power Supplies
- Battery-Charger Circuits


## TYPICAL APPLICATION



AiT Semiconductor Inc.

PIN DESCRIPTION


AiT Semiconductor Inc.

## ABSOLUTE MAXIMUM RATINGS

| $V_{\text {DD }}$, Input Voltage |  | 7.0V |
| :---: | :---: | :---: |
| VEN, EN to GND Voltage |  | -0.3V ~ 7.0V |
| $\mathrm{P}_{\mathrm{D}}$, Power Dissipation, $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | SOT-25 | 0.25 W |
| $\theta_{\mathrm{JA}}$, Thermal Resistance | SOT-25 | $250^{\circ} \mathrm{C} / \mathrm{W}$ |
| Lead Temperature (Soldering, 10 sec .) |  | $260^{\circ} \mathrm{C}$ |
| Tsta, Storage Temperature Range |  | $-65^{\circ} \mathrm{C} \sim 150^{\circ} \mathrm{C}$ |
| Operating Ambient Temperature |  | $-20^{\circ} \mathrm{C} \sim 100^{\circ} \mathrm{C}$ |
| ESD Susceptibility | HBM | 6000 V |
|  | MM | 600 V |

Stress beyond above listed "Absolute Maximum Ratings" may lead permanent damage to the device. These are stress ratings only and operations of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## ELECTRICAL CHARACTERISTICS

$\mathrm{V}_{\mathbb{I}}=5 \mathrm{~V}, \mathrm{C}_{\mathbb{I N}}=\mathrm{C}_{\text {out }}=1 \mu \mathrm{~F}$, unless otherwise noted. Typical values are at $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$.

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Input Voltage Range | VIN |  | 2.2 | - | 6 | V |
| NMOS Output On-Resistance | RDS(0N) | $\mathrm{LL}=500 \mathrm{~mA}$ | - | 150 | 200 | $\mathrm{m} \Omega$ |
| Quiescent Current | 1 Q | $\mathrm{V}_{\text {IN }}=3 \mathrm{~V}$ | - | 19 | 40 | $\mu \mathrm{A}$ |
|  |  | $\mathrm{V}_{\text {IN }}=5 \mathrm{~V}$ | - | 23 | 45 |  |
| Turn-On Time | $t_{R}$ | $\mathrm{R}_{\mathrm{L}}=10 \Omega, 90 \%$ Settling | - | 400 | - | $\mu \mathrm{s}$ |
| Current Limit Setting | ІІimit | A4770AE5R-A, RL $=2 \Omega$ | 0.9 | 1 | 1.1 | A |
|  |  | A4770AE5R-B, $\mathrm{R}_{\mathrm{L}}=2 \Omega$ | 0.6 | 0.65 | 0.7 |  |
| EN PIN Input High Voltage | - |  | 1.5 | - | - | V |
| EN PIN Input Low Voltage | - |  | - | - | 0.8 | V |
| Shutdown Current | loff | $\mathrm{EN}=$ "0" | - | 0.1 | 1 | $\mu \mathrm{A}$ |
| Output Leakage Current | Ileakage | $\mathrm{EN}=$ " 0 ", $\mathrm{V}_{\text {OUt }}=0 \mathrm{~V}$ | - | 0.5 | 10 | $\mu \mathrm{A}$ |
| VIn Under Voltage Lockout | UVLO |  | 1.3 | 1.8 | - | V |
| VIN Under Voltage Hysteresis | - |  | - | 100 | - | mV |
| Thermal Limit | Tsd |  | - | 130 | - | ${ }^{\circ} \mathrm{C}$ |
| Thermal Limit Hysteresis | $\Delta T_{\text {sd }}$ |  | - | 20 | - | ${ }^{\circ} \mathrm{C}$ |

AiT Semiconductor Inc.

## BLOCK DIAGRAM



AiT Semiconductor Inc.

## PACKAGE INFORMATION

Dimension in SOT-25 (Unit: mm)


| Symbol | Millimeters |  | Inches |  |
| :---: | :---: | :---: | :---: | :---: |
|  | Min | Max | Min | Max |
| A | 1.050 | 1.250 | 0.041 | 0.049 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 1.050 | 1.150 | 0.041 | 0.045 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.100 | 0.200 | 0.004 | 0.008 |
| D | 2.820 | 3.020 | 0.111 | 0.119 |
| E | 1.500 | 1.700 | 0.059 | 0.067 |
| E1 | 2.650 | 2.950 | 0.104 | 0.116 |
| e | 0.950 BSC |  |  | 0.037 BSC |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.300 | 0.600 | 0.012 | 0.024 |
| $\theta$ | $0^{\circ}$ | $8^{\circ}$ | $0^{\circ}$ | $8^{\circ}$ |

## IMPORTANT NOTICE

AiT Semiconductor Inc. (AiT) reserves the right to make changes to any its product, specifications, to discontinue any integrated circuit product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

AiT Semiconductor Inc.'s integrated circuit products are not designed, intended, authorized, or warranted to be suitable for use in life support applications, devices or systems or other critical applications. Use of AiT products in such applications is understood to be fully at the risk of the customer. As used herein may involve potential risks of death, personal injury, or servere property, or environmental damage. In order to minimize risks associated with the customer's applications, the customer should provide adequate design and operating safeguards.

AiT Semiconductor Inc. assumes to no liability to customer product design or application support. AiT warrants the performance of its products of the specifications applicable at the time of sale.

